Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	6158	transistor and finger and measur$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 07:58
L2	42	1 and "716"/$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 07:53
L3	13926	transistor and (parameter same measur$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 07:59
L4	74	3 and 716/5.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 07:59
L5	69	4 not 2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 10:06
L6	956342	(lvs or (layout near3 schematic))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 10:07
L7	190	(lvs or (layout near3 schematic)) and mark$3 near3 shape	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 10:19
L8	12	7 and "716"/$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 10:07
L9	507	(lvs or (layout near3 schematic)) and finger and measur$3 and parameter	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 10:19

L10	8	9 and "716"/$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 10:19
S65	1064	(716/5).CCLS.	USPAT; USOCR	OR	OFF	2005/10/27 07:53
S66	1309	(716/4).CCLS.	USPAT; USOCR	OR	OFF	2005/10/25 09:47
S67	4075	(transistor or fet or field near3 effect or soi or silicon near3 insulator or bipolar or bjt or hetero near3 junction or hbt) and "716"/$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/25 09:49
S68	3848	(transistor or fet or field near3 effect or soi or silicon near3 insulator or bipolar or bjt or hetero near3 junction or hbt) same finger	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/25 09:49
S69	8	(transistor or fet or field near3 effect or soi or silicon near3 insulator or bipolar or bjt or hetero near3 junction or hbt) same finger and netlist and measur$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/25 09:55
S70	95	(transistor or fet or field near3 effect or soi or silicon near3 insulator or bipolar or bjt or hetero near3 junction or hbt) same finger and (lvs or layout near2 schematic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/25 09:55
S71	95	(transistor or fet or field near3 effect or soi or silicon near3 insulator or bipolar or bjt or hetero near3 junction or hbt) same finger and (lvs or layout near2 schematic or layout near3 verif$7)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/25 09:56
S72	91	S71 not S69	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/25 09:56
S73	2480	sub near3 circuit and measur$3 and (lvs or schematic or drc or design near3 check)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/25 10:31
S74	32	S73 and S65	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/25 10:33

S75	8965	finger same lvs or layout near3 schematic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/25 10:36
S76	89	S75 and S65	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/25 10:34
S77	127	S71 S72 S74	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/25 10:34
S78	78	S76 not S77	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/25 10:34
S79	7861	finger and (lvs or layout near3 schematic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/25 10:37
S80	2	S79 and S65	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/25 10:37